METHOD OF MANUFACTURING BONDED WAFER

ABSTRACT

The present invention provides a method of manufacturing a bonded wafer. The method comprises an oxidation step in which an oxide film is formed on at least one surface of a base wafer, a bonding step in which the base wafer on which the oxide film has been formed is bonded to a top wafer to form a bonded wafer, and a thinning step in which the top wafer included in the bonded wafer is thinned.. The oxidation step comprises heating the base wafer to a heating temperature ranging from 800 to 1300 °C at a rate of temperature increase ranging from 1 to 300 °C/second in an oxidizing atmosphere, and the bonding step is carried out so as to position the oxide film formed in the oxidation step at an interface of the top wafer and the base wafer.